

High Voltage Power MOSFETs

IXTH02N250 IXTV02N250S

$$V_{DSS} = 2500V$$

$$I_{D25} = 200mA$$

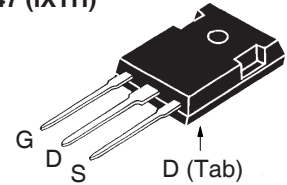
$$R_{DS(on)} \leq 450\Omega$$

N-Channel Enhancement Mode
Fast Intrinsic Diode

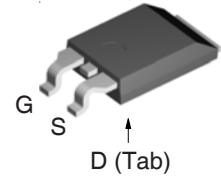


| Symbol | Test Conditions | Maximum Ratings | |
|------------|---|-------------------|------------|
| V_{DSS} | $T_J = 25^\circ C$ to $150^\circ C$ | 2500 | V |
| V_{DGR} | $T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$ | 2500 | V |
| V_{GSS} | Continuous | ± 20 | V |
| V_{GSM} | Transient | ± 30 | V |
| I_{D25} | $T_C = 25^\circ C$ | 200 | mA |
| I_{DM} | $T_C = 25^\circ C$, Pulse Width Limited by T_{JM} | 600 | mA |
| P_D | $T_C = 25^\circ C$ | 83 | W |
| T_J | | - 55 ... +150 | $^\circ C$ |
| T_{JM} | | 150 | $^\circ C$ |
| T_{stg} | | - 55 ... +150 | $^\circ C$ |
| T_L | 1.6mm (0.062 in.) from Case for 10s | 300 | $^\circ C$ |
| T_{SOLD} | Plastic Body for 10s | 260 | $^\circ C$ |
| M_d | Mounting Torque (TO-247) | 1.13 / 10 | Nm/lb.in |
| F_C | Mounting Force (PLUS220) | 11..65 / 25..14.6 | N/lb. |
| Weight | TO-247 | 6 | g |
| | PLUS220 | 4 | g |

TO-247 (IXTH)



PLUS220SMD (IXTV_S)



G = Gate D = Drain
S = Source Tab = Drain

Features

- Fast Intrinsic Diode
- Low Package Inductance

Advantages

- Easy to Mount
- Space Savings

Applications

- High Voltage Power Supplies
- Capacitor Discharge
- Pulse Circuits

| Symbol | Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|--------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 250\mu A$ | 2500 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ | 2.5 | | 4.5 V |
| I_{GSS} | $V_{GS} = \pm 20V$, $V_{DS} = 0V$ | | | ± 100 nA |
| I_{DSS} | $V_{DS} = 0.8 \cdot V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$ | | | 5 μA |
| | | | | 500 μA |
| $R_{DS(on)}$ | $V_{GS} = 10V$, $I_D = 50mA$, Note 1 | | | 450 Ω |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|--|-----------------------|------|--------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 100\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1 | 88 | 145 | mS |
| C_{iss} | $V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$ | | 116 | pF |
| C_{oss} | | | 8 | pF |
| C_{rss} | | | 3 | pF |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 100\Omega$ (External) | | 19 | ns |
| t_r | | | 19 | ns |
| $t_{d(off)}$ | | | 32 | ns |
| t_f | | | 33 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ | | 7.4 | nC |
| Q_{gs} | | | 0.7 | nC |
| Q_{gd} | | | 5.3 | nC |
| R_{thJC} | | | 1.5 | $^\circ\text{C/W}$ |
| R_{thCS} | | 0.25 | | $^\circ\text{C/W}$ |

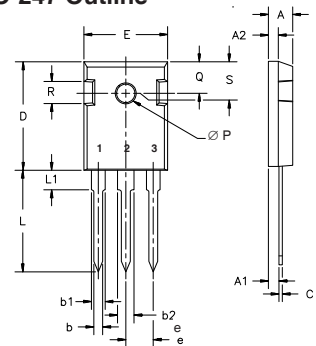
Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|----------|--|-----------------------|------|---------------|
| | | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0\text{V}$ | | | 200 mA |
| I_{SM} | Repetitive, Pulse Width Limited by T_{JM} | | | 800 mA |
| V_{SD} | $I_F = 100\text{mA}$, $V_{GS} = 0\text{V}$, Note 1 | | | 2.0 V |
| t_{rr} | $I_F = 200\text{mA}$, $-di/dt = 50\text{A}/\mu\text{s}$, $V_R = 100\text{V}$ | | 1.5 | μs |

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

*Additional provisions for lead to lead voltage isolation are required at $V_{DS} > 1200\text{V}$.

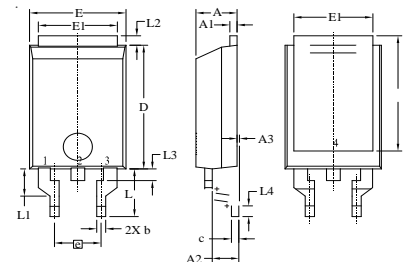
TO-247 Outline



Terminals: 1 - Gate
2 - Drain
3 - Source

| Dim. | Millimeter | | Inches | |
|----------------|------------|-------|---------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.7 | 5.3 | .185 | .209 |
| A ₁ | 2.2 | 2.54 | .087 | .102 |
| A ₂ | 2.2 | 2.6 | .059 | .098 |
| b | 1.0 | 1.4 | .040 | .055 |
| b ₁ | 1.65 | 2.13 | .065 | .084 |
| b ₂ | 2.87 | 3.12 | .113 | .123 |
| C | .4 | .8 | .016 | .031 |
| D | 20.80 | 21.46 | .819 | .845 |
| E | 15.75 | 16.26 | .610 | .640 |
| e | 5.20 | 5.72 | 0.205 | 0.225 |
| L | 19.81 | 20.32 | .780 | .800 |
| L ₁ | | 4.50 | | .177 |
| ∅P | 3.55 | 3.65 | .140 | .144 |
| Q | 5.89 | 6.40 | 0.232 | 0.252 |
| R | 4.32 | 5.49 | .170 | .216 |
| S | 6.15 BSC | | 242 BSC | |

PLUS220SMD Outline



1. Gate 2. Drain
3. Source 4. Drain

| SYM | INCHES | | MILLIMETER | |
|----------------|---------|------|------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .169 | .185 | 4.30 | 4.70 |
| A ₁ | .028 | .035 | 0.70 | 0.90 |
| A ₂ | .098 | .118 | 2.50 | 3.00 |
| A ₃ | .000 | .010 | 0.00 | 0.25 |
| b | .035 | .047 | 0.90 | 1.20 |
| b ₁ | .080 | .095 | 2.03 | 2.41 |
| b ₂ | .054 | .064 | 1.37 | 1.63 |
| c | .028 | .035 | 0.70 | 0.90 |
| D | .551 | .591 | 14.00 | 15.00 |
| D ₁ | .512 | .539 | 13.00 | 13.70 |
| E | .394 | .433 | 10.00 | 11.00 |
| E ₁ | .331 | .346 | 8.40 | 8.80 |
| e | .200BSC | | 5.08 BSC | |
| L | .209 | .228 | 5.30 | 5.80 |
| L ₁ | .118 | .138 | 3.00 | 3.50 |
| L ₂ | .035 | .051 | 0.90 | 1.30 |
| L ₃ | .045 | .053 | 1.25 | 1.35 |
| L ₄ | .039 | .059 | 1.00 | 1.50 |

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

| | | | | | | | | | |
|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

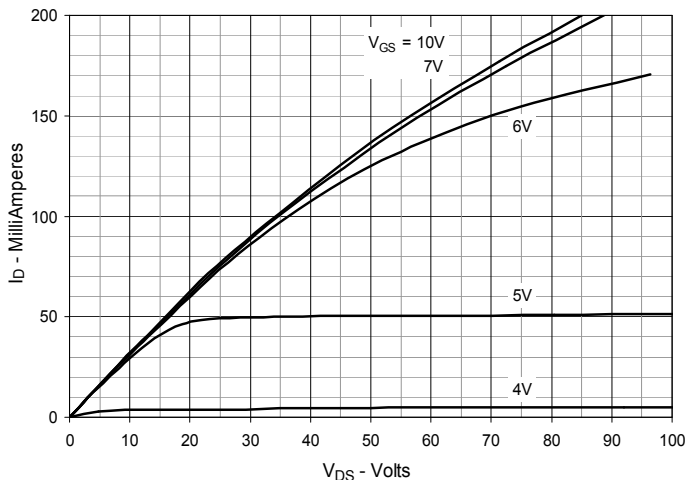


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

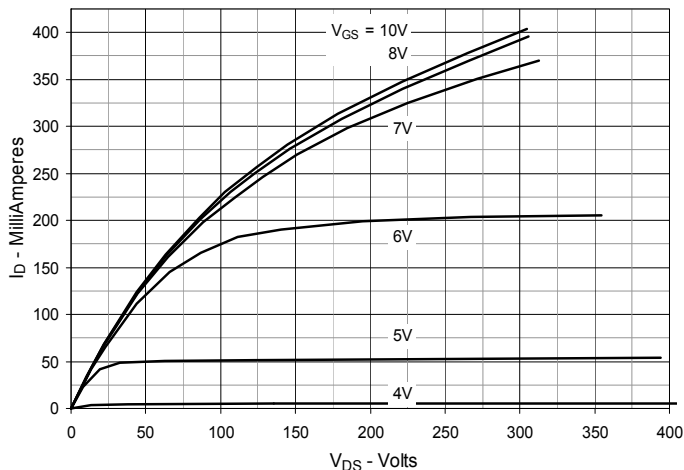


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

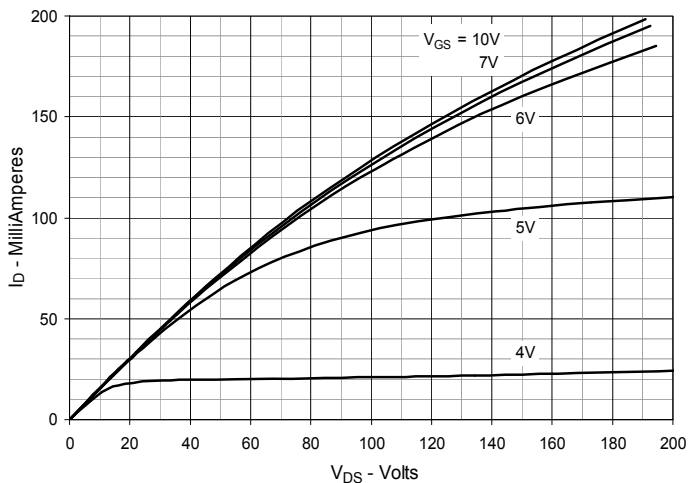


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 100\text{mA}$ Value vs. Junction Temperature

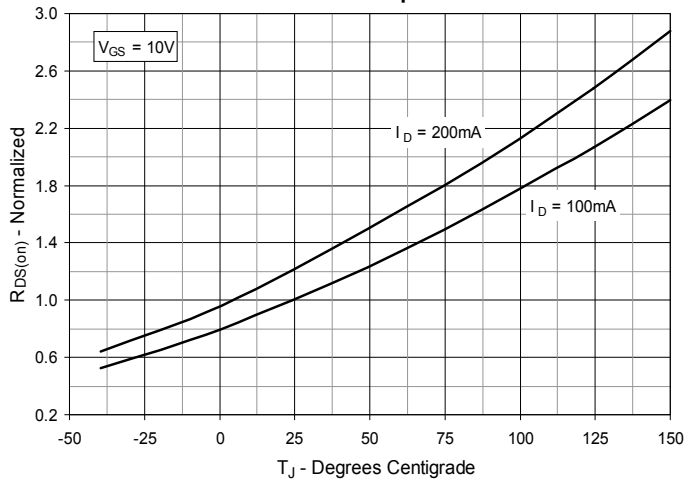


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 100\text{mA}$ Value vs. Drain Current

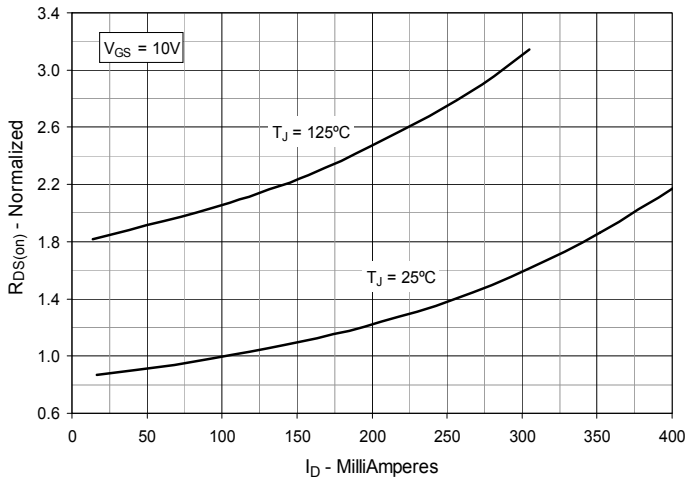


Fig. 6. Maximum Drain Current vs. Case Temperature

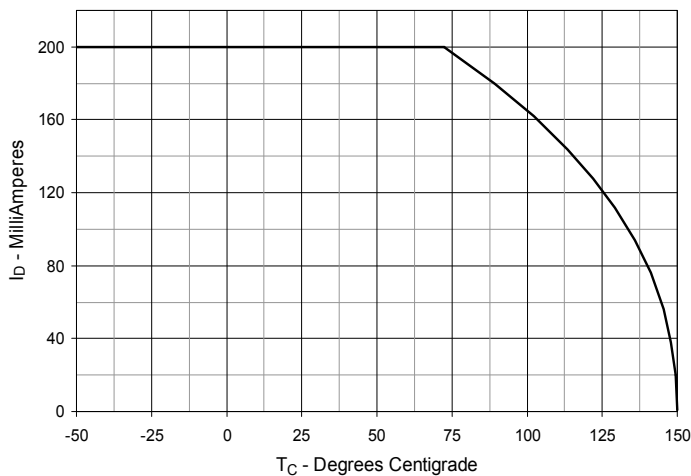


Fig. 7. Input Admittance

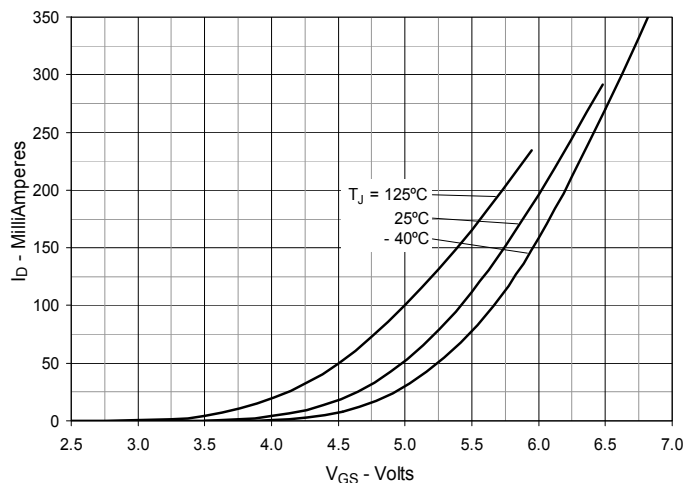


Fig. 8. Transconductance

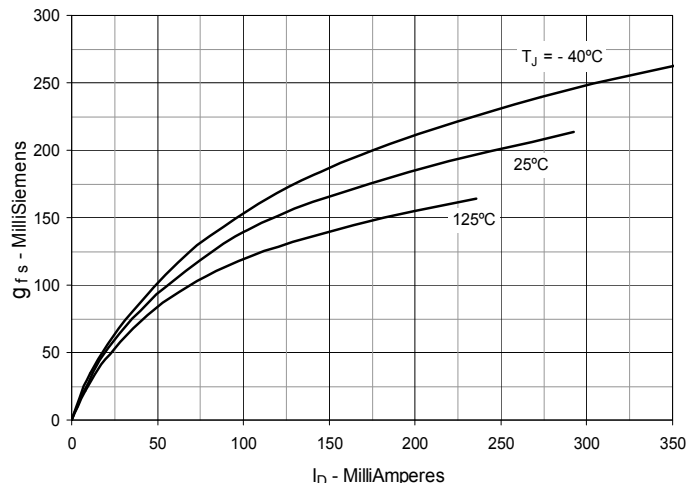


Fig. 9. Forward Voltage Drop of Intrinsic Diode

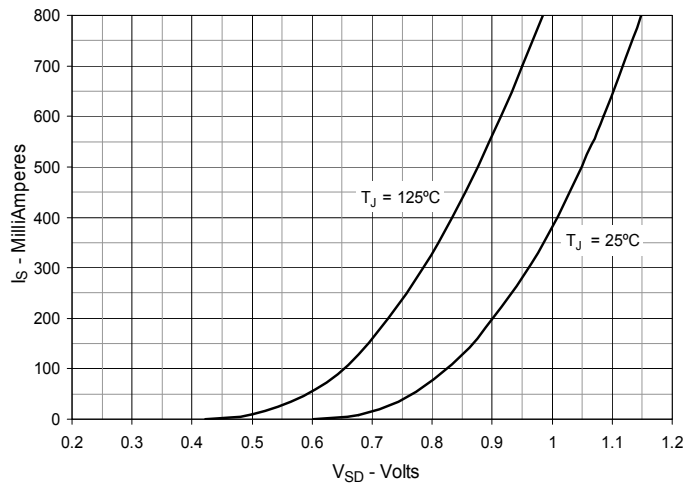


Fig. 10. Gate Charge

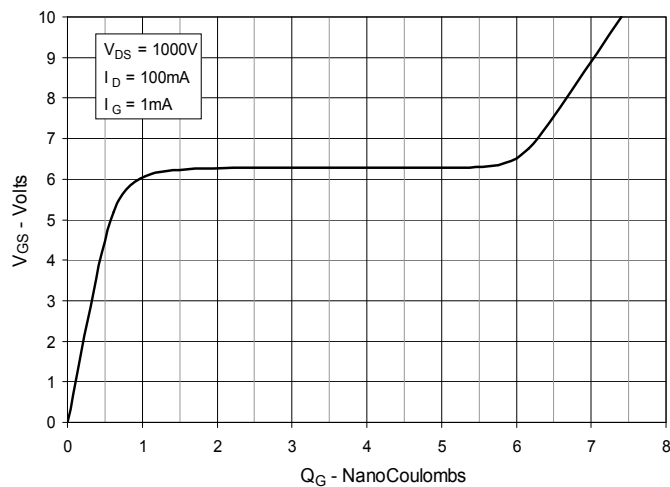


Fig. 11. Capacitance

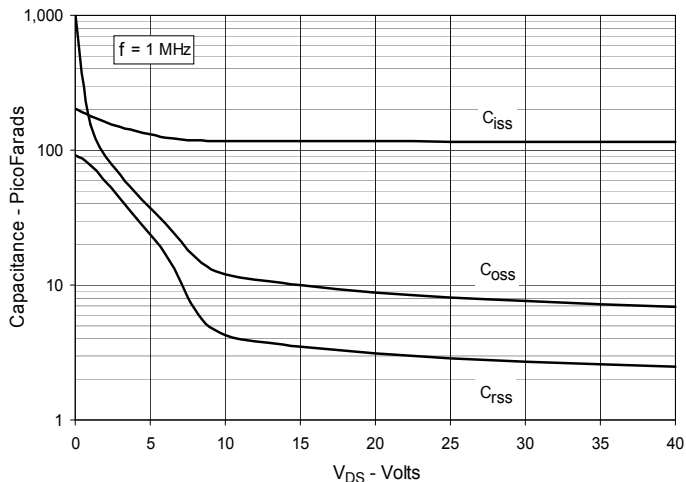


Fig. 12. Maximum Transient Thermal Impedance

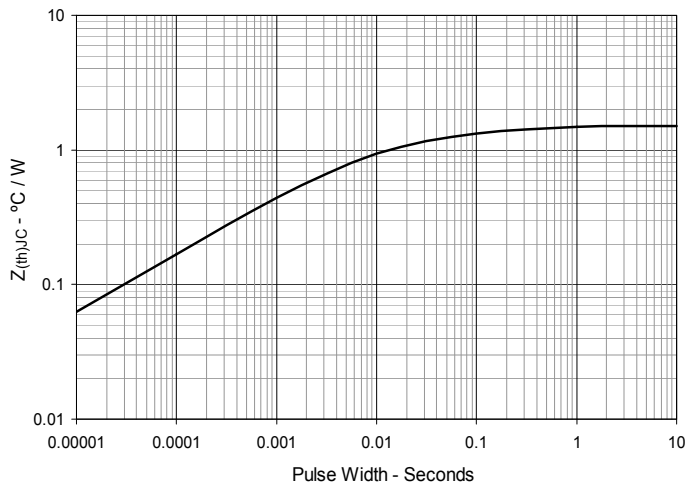


Fig. 13. Forward-Bias Safe Operating Area
@ $T_C = 25^\circ\text{C}$

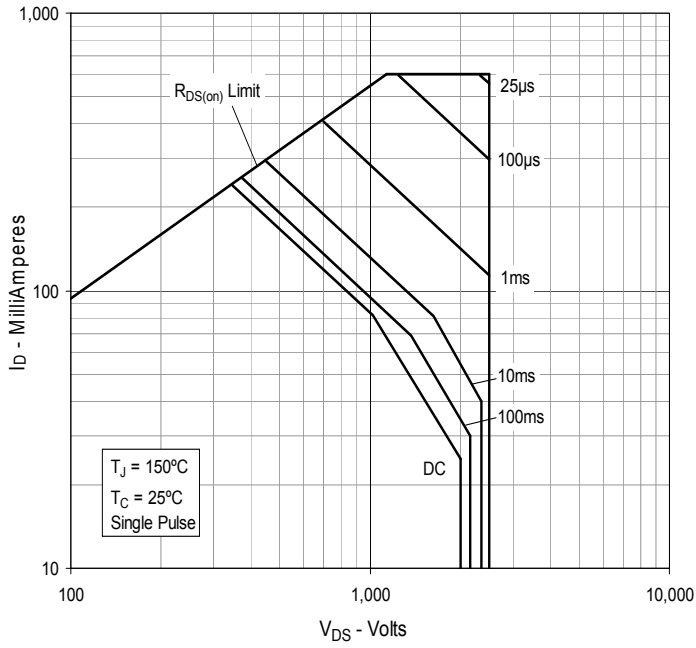
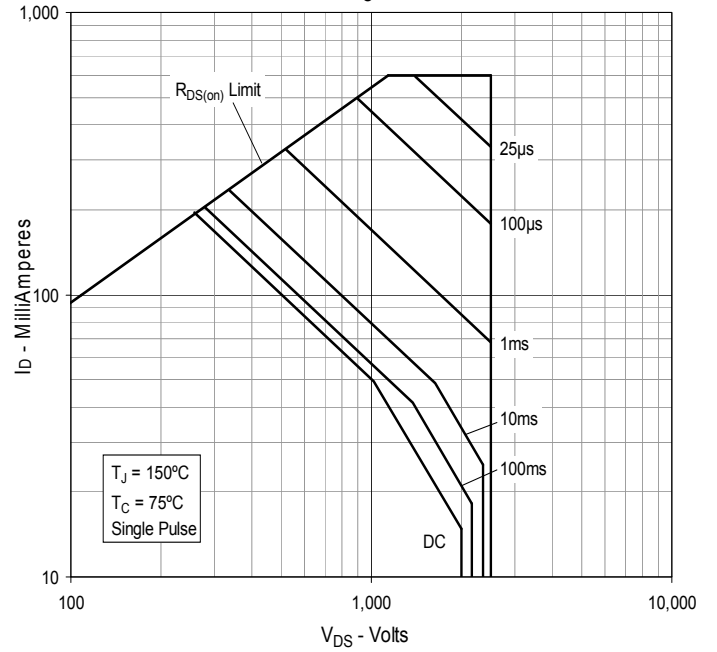


Fig. 14. Forward-Bias Safe Operating Area
@ $T_C = 75^\circ\text{C}$





Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.